





#### United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/504,782	02/15/2000	Masahiro Kume	0819-337	8307
22204	7590 03/31/2003			
NIXON PEABODY, LLP 8180 GREENSBORO DRIVE SUITE 800			EXAMINER	
			FLORES RUIZ, DELMA R	
MCLEAN, VA 22102			ART UNIT	PAPER NUMBER
			2828	
		DATE MAILED: 03/31/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

· ·	Application.	Applicant(s)			
Office Action Comments	09/504,782	KUME ET AL.			
Office Action Summary	Examiner .	Art Unit			
	Delma R. Flores Ruiz	2828			
The MAILING DATE of this communication apperiod for Reply	ppears on the cover sheet with	the correspondence address			
A SHORTENED STATUTORY PERIOD FOR REPI THE MAILING DATE OF THIS COMMUNICATION  - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a report of 18 No period for reply is specified above, the maximum statutory period for reply within the set or extended period for reply will, by statute any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).  Status	136(a). In no event, however, may a repl ply within the statutory minimum of thirty (; d will apply and will expire SIX (6) MONTH te, cause the application to become ABAN	y be timely filed  30) days will be considered timely. IS from the mailing date of this communication. IDONED (35 U.S.C. § 133).			
1)⊠ Responsive to communication(s) filed on <u>26</u>	December 2002 .				
2a)⊠ This action is <b>FINAL</b> . 2b)□ T	his action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the ments is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.  Disposition of Claims					
4)⊠ Claim(s) <u>1-6</u> is/are pending in the application	1.				
4a) Of the above claim(s) 7-35 is/are withdraw	vn from consideration.	0 - 0-			
4a) Of the above claim(s) <u>7-35</u> is/are withdrawn from consideration.  5) ☐ Claim(s) is/are allowed.					
6)⊠ Claim(s) <u>1-6</u> is/are rejected. PAUL IP					
7) ☐ Claim(s) is/are objected to. SUPERVISORY PATENT EXAMI					
8) Claim(s) are subject to restriction and/	or election requirement.	TECHNOLOGY CENTER 2800			
Application Papers					
9)☐ The specification is objected to by the Examiner.					
10)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.					
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).					
11)☐ The proposed drawing correction filed on is: a)☐ approved b)☐ disapproved by the Examiner.					
If approved, corrected drawings are required in reply to this Office action.					
12) The oath or declaration is objected to by the Examiner.					
Priority under 35 U.S.C. §§ 119 and 120					
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).					
a) All b) Some * c) None of:					
1. Certified copies of the priority documents have been received.					
<ul> <li>2. Certified copies of the priority documents have been received in Application No</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage</li> </ul>					
3. Copies of the certified copies of the pri- application from the International B  * See the attached detailed Office action for a lis	ureau (PCT Rule 17.2(a)).				
14) ☐ Acknowledgment is made of a claim for domes	tic priority under 35 U.S.C. §	119(e) (to a provisional application).			
a) ☐ The translation of the foreign language portion 15)☐ Acknowledgment is made of a claim for domes					
Attachment(s)					
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) Notice of Info	mmary (PTO-413) Paper No(s) ormal Patent Application (PTO-152)			
U.S. Patent and Trademark Office PTO-326 (Rev. 04-01) Office A	Action Summary	Part of Paper No. 11			

Art Unit: 2828

#### **DETAILED ACTION**

# Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 1 – 6 are recites the limitation " $x \ge y$ " in claim 1, line 11 and claim 4, line

12. There is insufficient antecedent basis for this limitation in the claim.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Art Unit: 2828

Claims 1 – 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Furukawa et al (5,981,977).

*Regarding claims 1* − *3,* Furukawa discloses a semiconductor laser device comprising; a first cladding (see Fig. 2C Character 24) layer, which is mace of a nitride semiconductor of a first conductivity type and is formed over a substrate (see Fig. 2C Character 12); an active layer (see Fig. 2C Character 26), which is mode of, which is made  $\ln_x \operatorname{Ga}_{1-x} \operatorname{N}$  layer and is formed over the first cladding layer; and a second cladding (see Fig. 2C Character 28) layer, which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer, wherein  $\ln_x \operatorname{Ga}_{1-x} \operatorname{N}$  layer of the first conductivity type is formed between the substrate and the first cladding layer and  $x \ge y$  in the composition on  $\ln$  (see Figs. 2A-D, Abstract, Column 1, lines 27 − 59, Column 2, lines 1 − 11, 29 − 44, 53 − 63, Column 4, lines 20 − 64). The spontaneous emission-absorbing layer contains indium and is formed in contact with the first cladding layer and substrate (see Fig. 2A-D, Column 8, lines 6 − 16, Column 10, lines 7 − 23).

Regarding claims 4 – 6, Furukawa discloses a semiconductor laser device comprising; a first cladding (see Fig. 2C Character 24) layer, which is mace of a nitride semiconductor of a first conductivity type and is formed over a substrate (see Fig. 2C Character 12); an active layer (see Fig. 2C Character 26) layer, which is mode of In<sub>x</sub> Ga<sub>1-x</sub>N and is formed over the first cladding layer; and a second cladding layer (see Fig.

Art Unit: 2828

2C Character 28), which is made of still another nitride semiconductor of a second conductivity type and is formed over the active layer, an electrode (see Fig. 1A Character 50 and 52) formed over the second cladding layer; wherein  $In_x$   $Ga_{1-x}N$  of the second conductivity type and is formed between the second cladding layer and  $x \succeq y$  in the composition on In and electrode (see Figs. 2A-D, Abstract, Column 1, lines 27 - 59, Column 2, lines 1 - 11, 29 - 44, 53 - 63, Column 4, lines 20 - 64). The spontaneous emission-absorbing layer contains indium and is formed in contact with the second cladding layer and electrode (see Fig. 2A-D, Column 8, lines 6 - 16, Column 10, lines 7 - 23).

## Response to Arguments

Applicant's arguments with respect to claims 1 – 6 have been considered but are moot in view of the new ground(s) of rejection. Applicants amendments raised new issues that made necessary the new art to be applied and therefore, the arguments presented against Furukawa are said to be moot due to the new grounds of rejection. Also, the arguments presented have been fully addressed in the above presented rejection.

Art Unit: 2828

### Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Delma R. Flores Ruiz whose telephone number is (703) 308-6238. The examiner can normally be reached on M - F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Paul Ip can be reached on (703) 308-3098. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 306-3431.

Examiner
Art Unit 2828

DRFR/PI March 20, 2003 Paul Ip Supervisor Patent Examiner Art Unit 2828